Bibliografia

- [1] A. Camplani, S. Shojaii, H. Shrimali, A. Stabile, and V. Liberali, "Cmos ic radiation hardening by design," *Facta universitatis series: Electronics and Energetics*, vol. 27, pp. 251–258, 01 2014.
- [2] L. Edmonds, C. Barnes, L. Scheick, U. S. N. Aeronautics, S. Administration, and J. P. L. (U.S.), An Introduction to Space Radiation Effects on Microelectronics, ser. JPL publication. Jet Propulsion Laboratory, National Aeronautics and Space Administration, 2000. [Online]. Available: https://books.google.it/books?id=3azqHAAACAAJ
- [3] F. B. McLean and T. R. Oldham, "Basic mechanisms of radiation effects in electronic materials and devices, final report, september 1986-september 1987," 9 1987. [Online]. Available: https://www.osti.gov/biblio/5646360
- [4] A. Ortiz-Conde, F. Garcia Sánchez, J. Liou, A. Cerdeira, M. Estrada, and Y. Yue, "A review of recent mosfet threshold voltage extraction methods," *Microelectronics Reliability*, vol. 42, no. 4, pp. 583–596, 2002. [Online]. Available: https://www.sciencedirect.com/science/article/pii/S0026271402000276
- [5] T. Rudenko, V. Kilchytska, M. K. M. Arshad, J.-P. Raskin, A. Nazarov, and D. Flandre, "Influence of drain voltage on mosfet threshold voltage determination by transconductance change and gm/id methods," in *Ulis 2011 Ultimate Integration on Silicon*, 2011, pp. 1–4.
- [6] J. Voves, "Nanoelectronics and nanolithography," vol. 10, 01 2009.